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November 2013

# FDI030N06

# N-Channel PowerTrench<sup>®</sup> MOSFET 60 V, 193 A, 3.2 m $\Omega$

#### **Features**

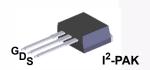
- $R_{DS(on)}$  = 2.6 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- · High Power and Current Handling Capability
- · RoHS Compliant

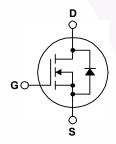
## Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

## **Applications**

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Renewable System





### **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise note.

| Symbol                            |  | Parameter                                    |              | FDI030N06   | Unit |
|-----------------------------------|--|--|--------------|-------------|------|
| $V_{DSS}$                         | Drain to Source Voltage  |  |              | 60          | V    |
| $V_{GSS}$                         | Gate to Source Voltage   | Gate to Source Voltage                       |              | ±20         | V    |
|                                   |  | - Continuous (T <sub>C</sub> = 25°C, Silico  | n Limited)   | 193*        |      |
| $I_D$                             | Drain Current  | - Continuous (T <sub>C</sub> = 100°C, Silice | on Limited)  | 136*        | Α    |
|                                   |  | - Continuous (T <sub>C</sub> = 25°C, Packa   | age Limited) | 120         |      |
| I <sub>DM</sub>                   | Drain Current  | - Pulsed                                     | (Note 1)     | 772         | Α    |
| E <sub>AS</sub>                   | Single Pulsed Avalanche  | e Energy                                     | (Note 2)     | 1434        | mJ   |
| dv/dt                             | Peak Diode Recovery dv   | //dt   | (Note 3)     | 6           | V/ns |
| В                                 | Dawar Dissipation  | (T <sub>C</sub> = 25°C)                      |              | 231         | W    |
| $P_{D}$                           | Power Dissipation  | - Derate Above 25°C                          |              | 1.54        | W/°C |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage  | Temperature Range                            |              | -55 to +175 | °C   |
| T <sub>L</sub>                    | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds |  |              | 300         | °C   |

<sup>\*</sup>Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

#### **Thermal Characteristics**

| Symbol          | Parameter                                     | FDI030N06 | Unit  |
|-----------------|---|-----------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max.    | 0.65      | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. | 62.5      | -C/VV |

# **Package Marking and Ordering Information**

| Part Number | Top Mark  | Package             | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-----------|---------------------|----------------|-----------|------------|----------|
| FDI030N06   | FDI030N06 | I <sup>2</sup> -PAK | Tube           | N/A       | N/A        | 50 units |

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

| Symbol                                  | Parameter                                 | Test Conditions                                      | Min. | Тур. | Max. | Unit |
|---|---|--|------|------|------|------|
| Off Charac                              | cteristics                                |  |      |      |      |      |
| $BV_{DSS}$                              | Drain to Source Breakdown Voltage         | $I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$  | 60   | -    | -    | V    |
| ΔBV <sub>DSS</sub><br>/ ΔT <sub>J</sub> | Breakdown Voltage Temperature Coefficient | I <sub>D</sub> = 1 mA, Referenced to 25°C            | -    | 0.05 | -    | V/°C |
| 1                                       | Zero Gate Voltage Drain Current           | V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V        | -    | -    | 1    | μА   |
| IDSS                                    | Zero Gate Voltage Drain Current           | $V_{DS} = 48 \text{ V}, T_{C} = 150^{\circ}\text{C}$ | -    | -    | 500  | μΑ   |
| $I_{GSS}$                               | Gate to Body Leakage Current              | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$    | -    | -    | ±100 | nA   |

#### **On Characteristics**

| V <sub>GS(th)</sub> | Gate Threshold Voltage               | $V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$      | 2.5 | 3.5 | 4.5 | V  |
|---------------------|--------------------------------------|---|-----|-----|-----|----|
| R <sub>DS(on)</sub> | Static Drain to Source On Resistance | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 A | -   | 2.6 | 3.2 | mΩ |
| 9 <sub>FS</sub>     | Forward Transconductance             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 75 A | -   | 154 | -   | S  |

#### **Dynamic Characteristics**

| C <sub>iss</sub>    | Input Capacitance             | V 05 V V 0 V  |        | -   | 7380 | 9815 | pF |
|---------------------|-------------------------------|---|--------|-----|------|------|----|
| Coss                | Output Capacitance            | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$<br>f = 1 MHz |        | -   | 1095 | 1455 | pF |
| C <sub>rss</sub>    | Reverse Transfer Capacitance  | 1 = 1 WH 12   |        | -\  | 415  | 625  | pF |
| Q <sub>g(tot)</sub> | Total Gate Charge at 10V      | V <sub>DS</sub> = 48 V, I <sub>D</sub> = 75 A,              |        | - \ | 116  | 151  | nC |
| Q <sub>gs</sub>     | Gate to Source Gate Charge    | V <sub>GS</sub> = 10 V                                      |        | -   | 40   | -    | nC |
| Q <sub>gd</sub>     | Gate to Drain "Miller" Charge | (No   | ote 4) | -   | 35   | -    | nC |

## **Switching Characteristics**

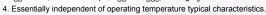
| t <sub>d(on)</sub>  | Turn-On Delay Time  |  | - | 39  | 87  | ns |
|---------------------|---------------------|--|---|-----|-----|----|
| t <sub>r</sub>      | Turn-On Rise Time   | $V_{DD} = 30 \text{ V}, I_{D} = 75 \text{ A},$ | - | 178 | 366 | ns |
| t <sub>d(off)</sub> | Turn-Off Delay Time | $V_{GS}$ = 10 V, $R_G$ = 4.7 $\Omega$          | - | 54  | 118 | ns |
| t <sub>f</sub>      | Turn-Off Fall Time  | (Note 4)                                       | - | 33  | 76  | ns |

#### **Drain-Source Diode Characteristics**

| I <sub>S</sub>  | Maximum Continuous Drain to Source Diode Forward Current |  | - | -  | 193 | Α  |
|-----------------|--|--|---|----|-----|----|
| I <sub>SM</sub> | Maximum Pulsed Drain to Source Diode Forward Current     |  | - | -  | 772 | Α  |
| $V_{SD}$        | Drain to Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A  | - | -  | 1.3 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                    | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A, | - | 46 | -   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                                  | $dI_F/dt = 100 A/\mu s$                        | - | 50 | -   | nC |

#### Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 0.51 mH, I  $_{AS}$  = 75 A, V  $_{DD}$  = 50 V, R  $_{G}$  = 25  $\!\Omega$  , starting T  $_{J}$  = 25  $\!^{\circ}$  C.
- 3. I  $_{SD}$   $\leq$  75 A, di/dt  $\leq$  450 A/ $\mu s,~V_{DD}$   $\leq$  BV  $_{DSS},$  starting T  $_{J}$  = 25°C.



## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

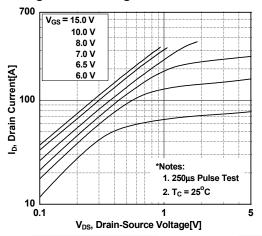


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

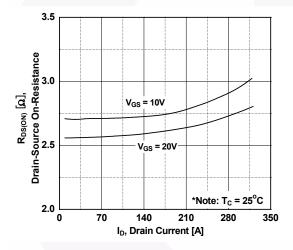


Figure 5. Capacitance Characteristics

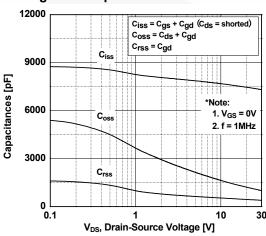


Figure 2. Transfer Characteristics

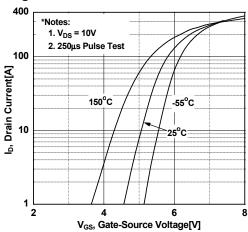


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

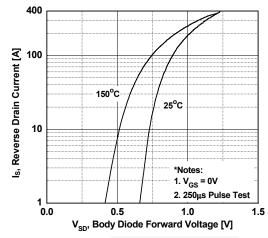
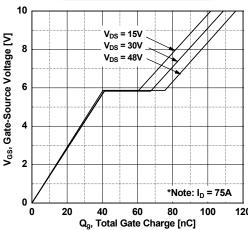


Figure 6. Gate Charge Characteristics



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

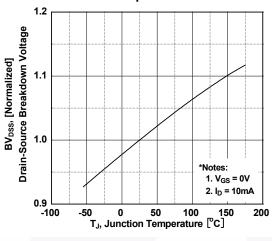


Figure 8. On-Resistance Variation vs. Temperature

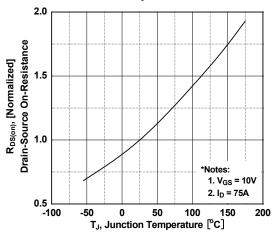


Figure 9. Maximum Safe Operating Area

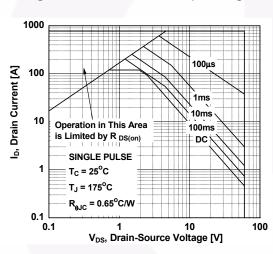


Figure 10. Maximum Drain Current vs. Case Temperature

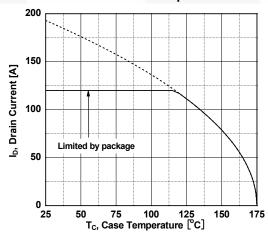
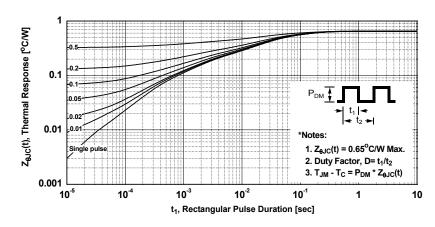


Figure 11. Transient Thermal Response Curve



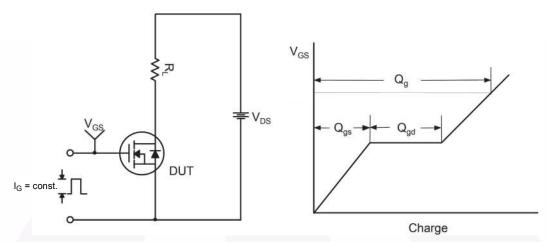


Figure 12. Gate Charge Test Circuit & Waveform

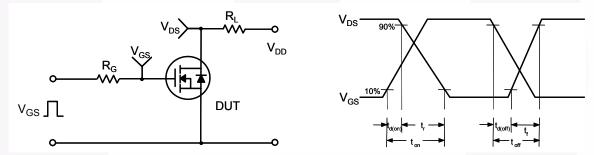


Figure 13. Resistive Switching Test Circuit & Waveforms

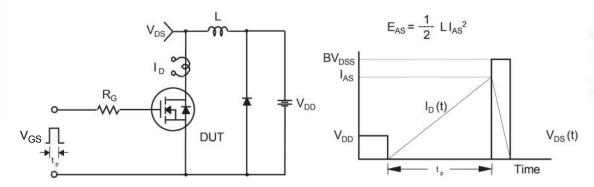


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

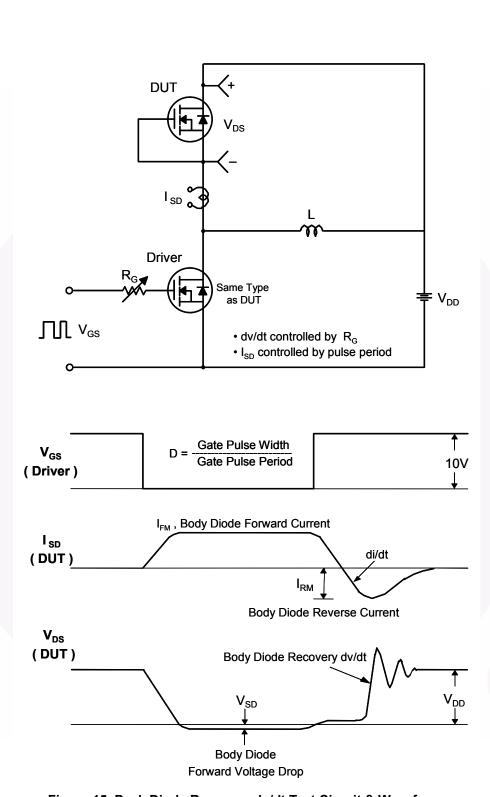
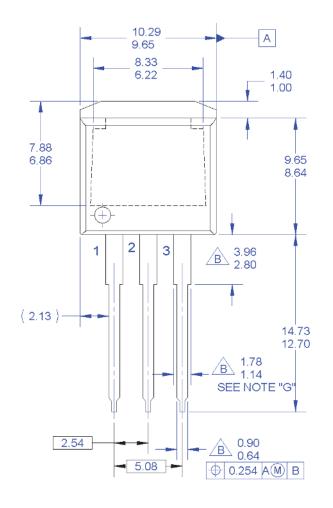
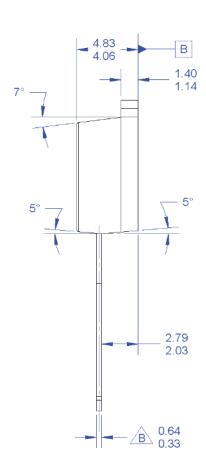


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**





#### NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO TO262 JEDEC VARIATION AA.

B. DOES NOT COMPLY JEDEC STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ANSI Y14.5-1994.
F. LOCATION OF PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF PACKAGE)
G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.
H. DRAWING FILE NAME: TO262A03REV5

# Figure 16. TO262 (I<sup>2</sup>PAK), Molded, 3-Lead, Jedec Variation AA

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